FAIRCHILD SEMICONDUCTOR®

April 2006

H11AA1-M, H11AA2-M, H11AA3-M, H11AA4-M AC Input/Phototransistor Optocouplers

Features

- Bi-polar emitter input
- Built-in reverse polarity input protection
- Underwriters Laboratory (UL) recognized File #E90700, Volume 2
- VDE approved File #102497 (ordering option 'V')

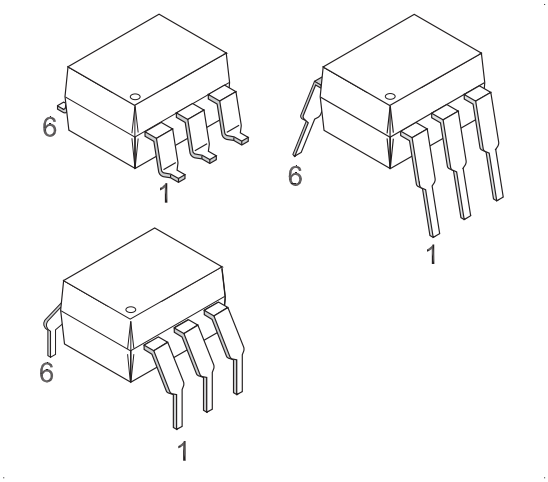
Applications

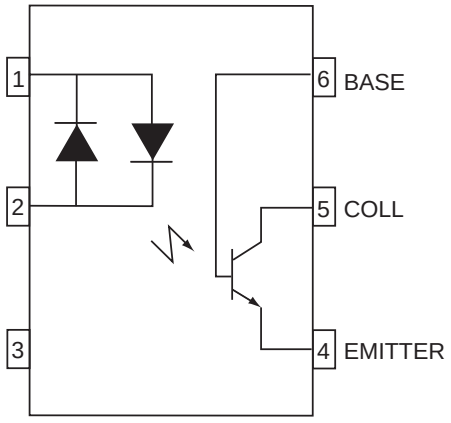
- AC line monitor
- Unknown polarity DC sensor
- Telephone line interface

Description

The H11AAX-M series consists of two gallium-arsenide infrared emitting diodes connected in inverse parallel driving a single silicon phototransistor output.

Package and Schematic





Absolute Maximum Ratings (T_A =25°C Unless otherwise specified)

Symbol	Parameter	Device	Value	Units
TOTAL DEVICE				
T_{STG}	Storage Temperature	All	-40 to +150	°C
T_{OPR}	Operating Temperature	All	-40 to +100	°C
T_{SOL}	Lead Solder Temperature	All	260 for 10 sec	°C
P_D	Total Device Power Dissipation	All	250	mW
	Derate Linearly From 25°C		2.94	mW/°C
EMITTER				
I_F	Continuous Forward Current	All	60	mA
I_F(pk)	Forward Current – Peak (1µs pulse, 300 pps)	All	±1.0	A
P_D	LED Power Dissipation	All	120	mW
	Derate Linearly From 25°C		1.41	mW/°C
DETECTOR				
I_C	Continuous Collector Current	All	50	mA
P_D	Detector Power Dissipation	All	150	mW
	Derate linearity from 25°C		1.76	mW/°C

Electrical Characteristics (T_A = 25°C Unless otherwise specified.)

Individual Component Characteristics

Symbol	Parameter	Test Conditions	Device	Min.	Typ.*	Max.	Unit
EMITTER							
V_F	Input Forward Voltage	I_F = ±10mA	All		1.17	1.5	V
C_J	Capacitance	V_F = 0 V, f = 1.0MHz	All		80		pF
DETECTOR							
BV_{CEO}	Breakdown Voltage Collector to Emitter	I_C = 1.0mA, I_F = 0	All	30	100		V
BV_{CBO}	Collector to Base	I_C = 100µA, I_F = 0	All	70	120		V
BV_{EBO}	Emitter to Base	I_E = 100µA, I_F = 0	All	5	10		V
BV_{ECO}	Emitter to Collector	I_E = 100µA, I_F = 0	All	7	10		V
I_{CEO}	Leakage Current Collector to Emitter	V_{CE} = 10 V, I_F = 0	H11AA1,3,4(-M)		1	50	nA
			H11AA2-M		1	200	
C_{CE}	Capacitance Collector to Emitter	V_{CE} = 0, f = 1MHz	All		10		pF
C_{CB}	Collector to Base	V_{CB} = 0, f = 1MHz	All		80		pF
C_{EB}	Emitter to Base	V_{EB} = 0, f = 1MHz	All		15		pF

*Typical values at T_A = 25°C

Transfer Characteristics (T_A = 25°C Unless otherwise specified.)

Symbol	Characteristics	Test Conditions	Device	Min.	Typ.*	Max.	Units
CTR_{CE}	Current Transfer Ratio, Collector to Emitter	I_F = ±10mA, V_{CE} = 10V	H11AA4-M	100			%
			H11AA3-M	50			
			H11AA1-M	20			
			H11AA2-M	10			
	Current Transfer Ratio, Symmetry	I_F = ±10mA, V_{CE} = 10V (Figure 11)	All	.33		3.0	
$V_{CE(SAT)}$	Saturation Voltage, Collector to Emitter	I_F = ±10mA, I_{CE} = 0.5mA	All			.40	V

Isolation Characteristics

Symbol	Characteristic	Test Conditions	Min.	Typ.*	Max.	Units
C_{I-O}	Package Capacitance Input/Output	V_{I-O} = 0, f = 1MHz		0.7		pF
V_{ISO}	Isolation Voltage	f = 60 Hz, t = 1 sec.	7500			Vac(pk)
R_{ISO}	Isolation Resistance	V_{I-O} = 500 VDC	10^{11}			Ω

*Typical values at T_A = 25°C

Typical Performance Characteristics

Fig. 1 Input Voltage vs. Input Current

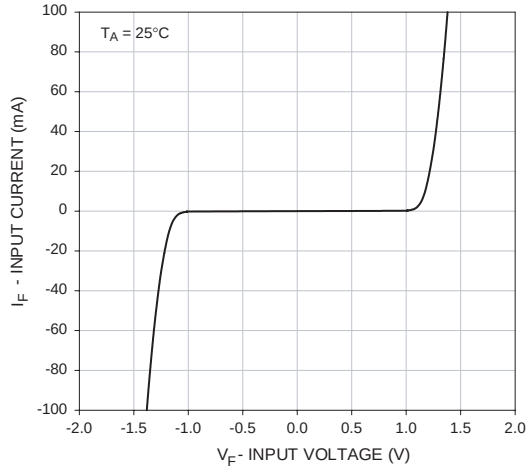


Fig. 2 Normalized CTR vs. Forward Current

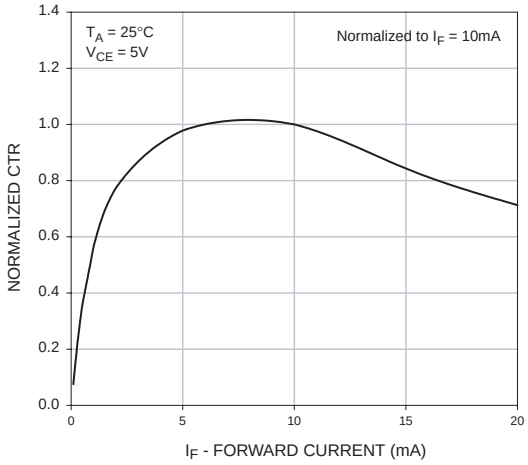


Fig. 3 Normalized CTR vs. Ambient Temperature

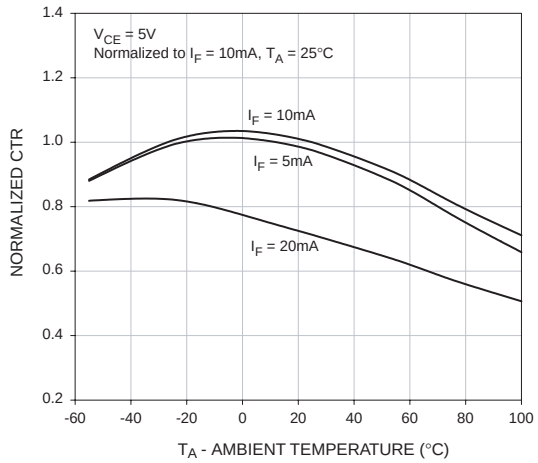


Fig. 4 CTR vs. RBE (Unsaturated)

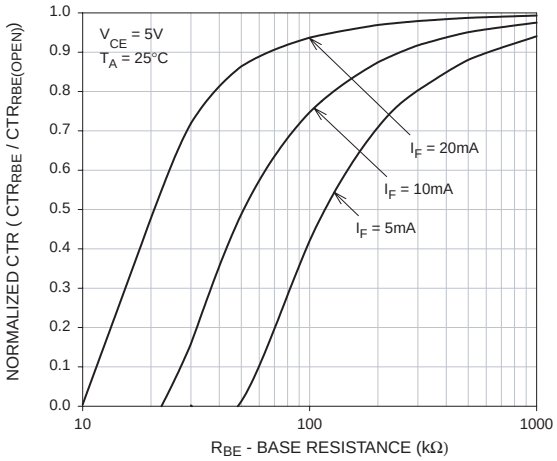


Fig. 5 CTR vs. RBE (Saturated)

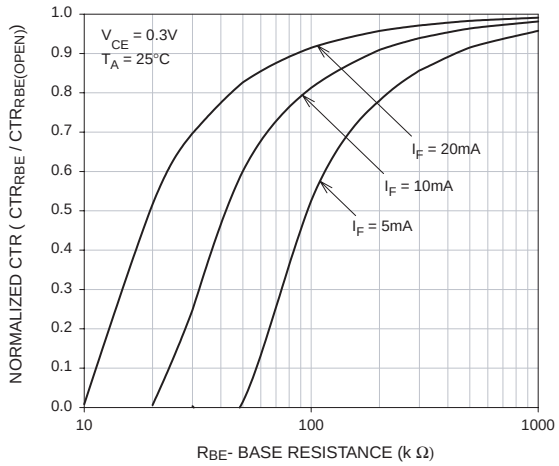
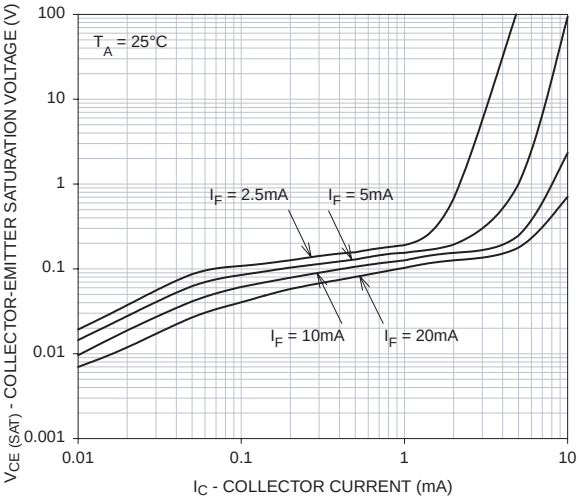


Fig. 6 Collector-Emitter Saturation Voltage vs Collector Current



Typical Performance Characteristics (Continued)

Fig. 7 Switching Speed vs. Load Resistor

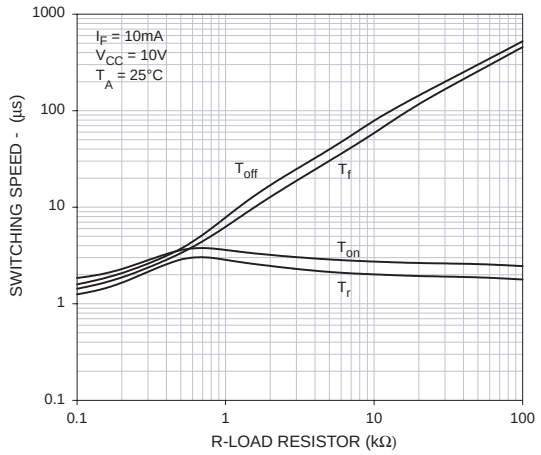


Fig. 8 Normalized t_{on} vs. R_{BE}

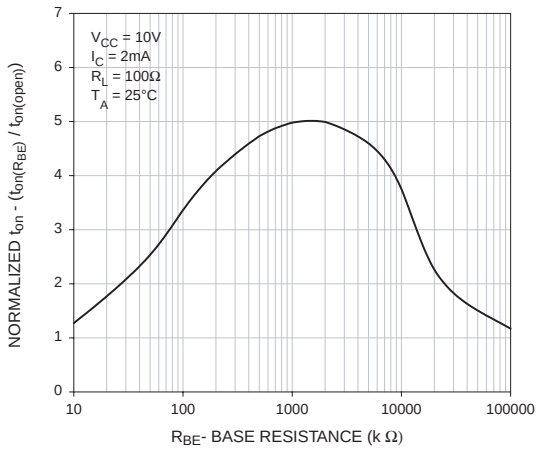


Fig. 9 Normalized t_{off} vs. R_{BE}

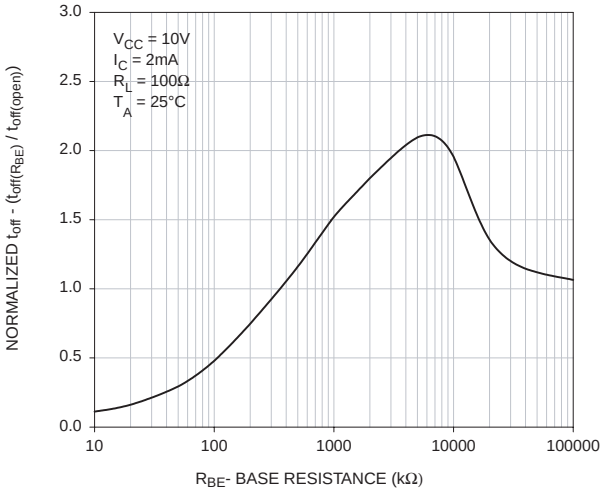


Fig. 10 Dark Current vs. Ambient Temperature

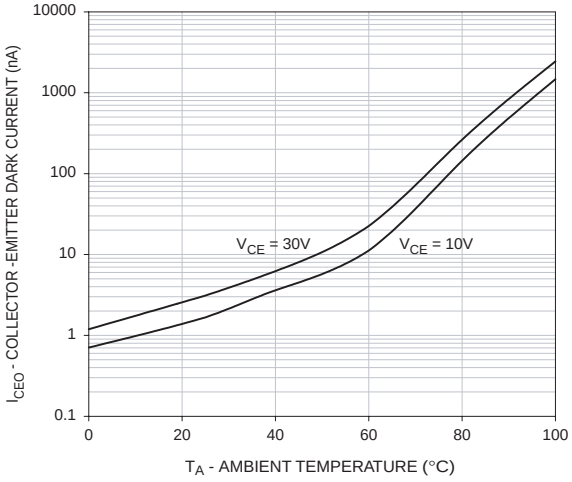
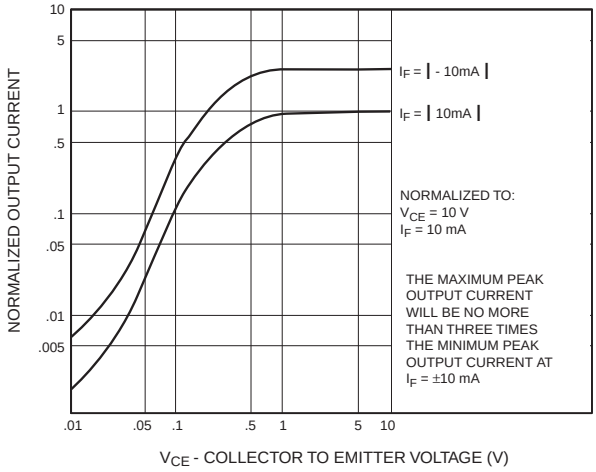
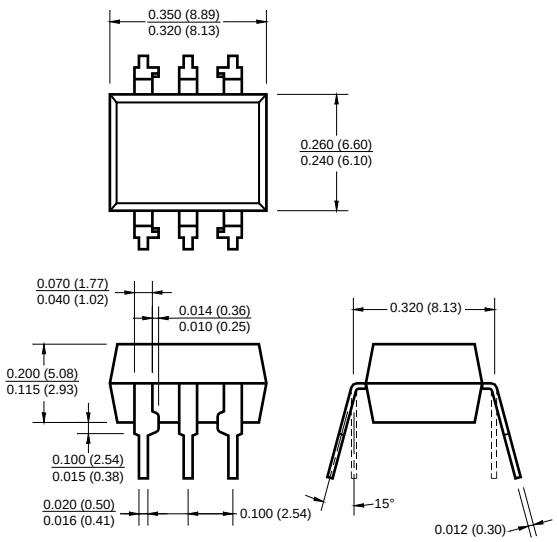


Fig. 11 Output Symmetry Characteristics

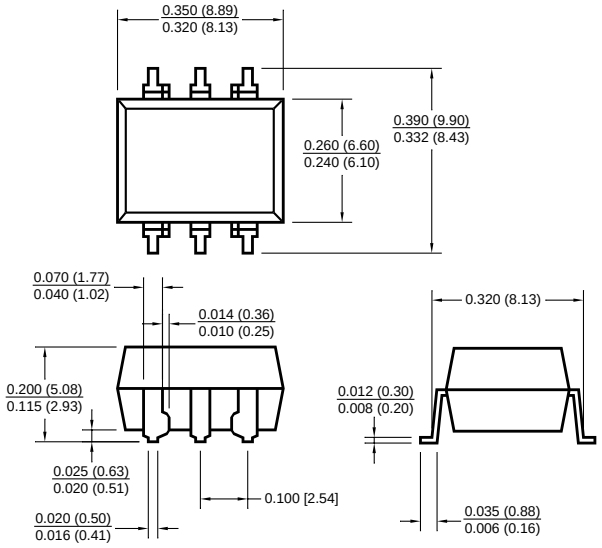


Mechanical Dimensions

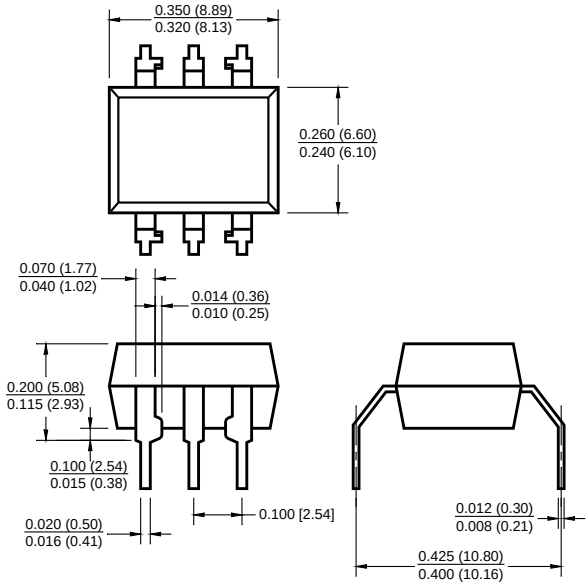
Package Dimensions (Through Hole)



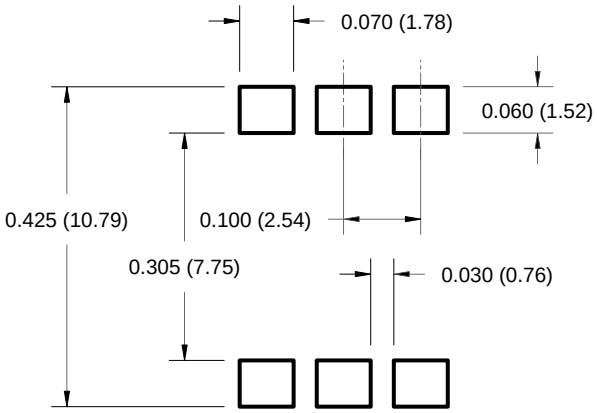
Package Dimensions (Surface Mount)



Package Dimensions (0.4" Lead Spacing)



Recommended Pad Layout for Surface MountLeadform

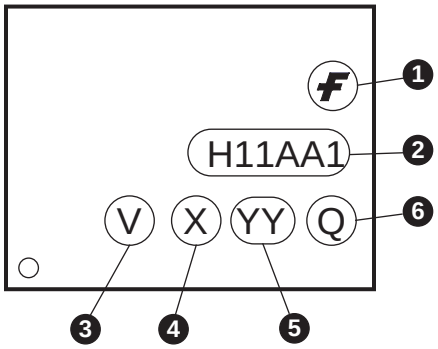


Note:
All dimensions are in inches (millimeters).

Ordering Information

Option/Order Entry Identifier	Description
S	Surface Mount Lead Bend
SR2	Surface Mount; Tape and Reel
T	0.4" Lead Spacing
V	VDE 0884
TV	VDE 0884, 0.4" Lead Spacing
SV	VDE 0884, Surface Mount
SR2V	VDE 0884, Surface Mount, Tape & Reel

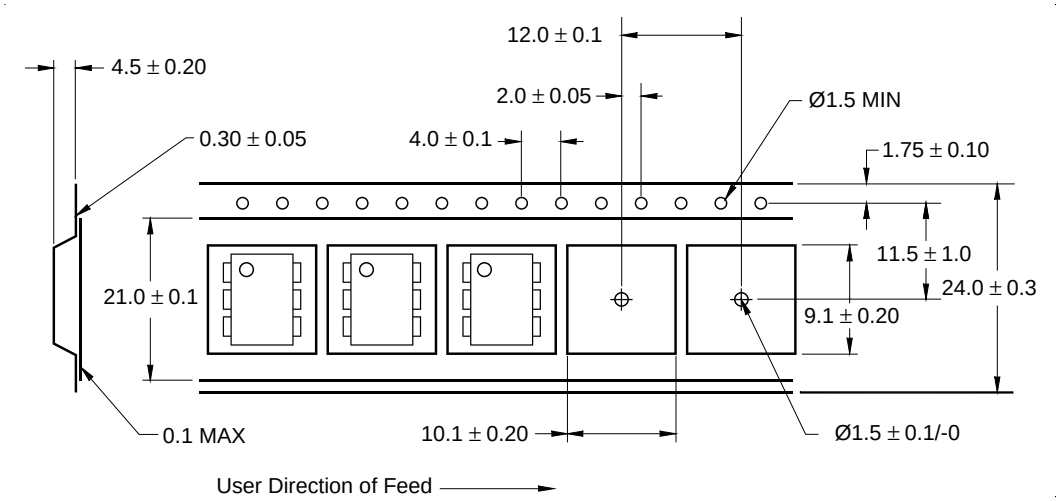
Marking Information



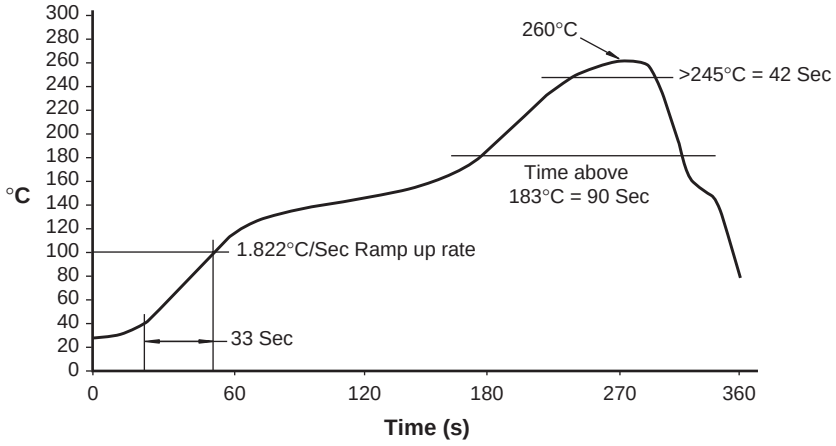
Definitions	
1	Fairchild logo
2	Device number
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)
4	One digit year code, e.g., '3'
5	Two digit work week ranging from '01' to '53'
6	Assembly package code

*Note – Parts that do not have the 'V' option (see definition 3 above) that are marked with date code '325' or earlier are marked in portrait format.

Carrier Tape Specifications



Reflow Profile (White Package, -M Suffix)



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EnSigna™	LittleFET™	PowerTrench®	TCM™	
FACT™	MICROCOUPLER™	QFET®	TinyBoost™	
FAST®	MicroFET™	QS™	TinyBuck™	
FASTr™	MicroPak™	QT Optoelectronics™	TinyPWM™	
FPS™	MICROWIRE™	Quiet Series™	TinyPower™	
FRFET™	MSX™	RapidConfigure™	TinyLogic®	
	MSXPro™	RapidConnect™	TINYOPTO™	
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The Power Franchise®		ScalarPump™	UHC™	
Programmable Active Droop™				

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
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